



General Description

The MAX15008 features a 300mA LDO regulator, a voltage tracker, and an overvoltage protection (OVP) controller to protect downstream circuits from high-voltage load dump. The MAX15010 includes only the 300mA LDO voltage regulator and voltage tracker. Both devices operate over a wide 5V to 40V supply voltage range and are able to withstand load-dump transients up to 45V. The MAX15008/MAX15010 feature short-circuit and thermalshutdown protection. These devices offer highly integrated power-management solutions for automotive applications such as instrument clusters, climate control, and a variety of automotive power-supply circuits.

The 300mA LDO regulator consumes less than 67µA quiescent current at light loads and is well suited to power always-on circuits during "key off" conditions. The LDO features independent enable and hold inputs as well as a microprocessor (µP) reset output with an adjustable reset timeout period.

The voltage tracker accurately (±3mV) tracks a voltage applied to its input from either the LDO output or an external source. It can supply up to 50mA of current to a remote sensor, allowing for precise ratiometric tracking in automotive applications. A separate enable input turns the tracker on or off, reducing supply current when the tracker is unused. The voltage tracker also features protection against battery reversal, an output short circuit to the battery, or an output-voltage excursion below ground potential to as much as -5V.

The MAX15008 OVP controller operates with an external enhancement mode n-channel MOSFET. While the monitored voltage remains below the adjustable threshold, the MOSFET stays on. When the monitored voltage exceeds the OVP threshold, the OVP controller quickly turns off the external MOSFET. The OVP controller is configurable as a load-disconnect switch or a voltage limiter.

The MAX15008/MAX15010 are available in a thermally enhanced, 32-pin (5mm x 5mm) TQFN package and are fully specified over the -40°C to +125°C automotive operating temperature range.

Applications

Instrument Clusters Climate Control AM/FM Radio Power Supply Multimedia Power Supply **Telematics Power Supply**

Typical Operating Circuits appear at end of data sheet.

Features

- 300mA LDO Regulator, Voltage Tracker, and OVP Controller (MAX15008)
- ♦ 300mA LDO Regulator and Voltage Tracker (MAX15010)
- ♦ 50mA Voltage Tracker with ±3mV Tracking Accuracy
- ♦ 5V to 40V Wide Operating Supply Voltage Range
- ◆ 45V Load Dump Protection
- ♦ 67µA Quiescent Current LDO Regulator
- ♦ OVP Controller Disconnects or Limits Output from **Battery Overvoltage Conditions (MAX15008)**
- ♦ LDO Regulator with Enable, Hold, and Reset **Features**

Ordering Information

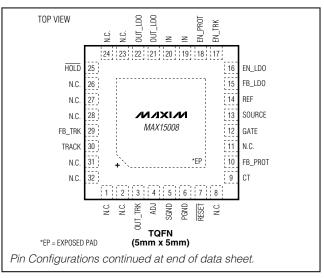
PART	TEMP RANGE	PIN- PACKAGE	PKG CODE	
MAX15008 ATJ+	-40°C to +125°C	32 TQFN-EP*	T3255-4	
MAX15010 ATJ+	-40°C to +125°C	32 TQFN-EP*	T3255-4	

⁺Denotes a lead-free package.

Selector Guide

PART	LDO	TRACKER	OVP CONTROLLER
MAX15008	$\sqrt{}$	\checkmark	√
MAX15010	V	\checkmark	_

Pin Configurations



Maxim Integrated Products 1

^{*}EP = Exposed pad.

ABSOLUTE MAXIMUM RATINGS

(All pins referenced to SGND, unless oth	,
IN, GATE	0.3V to +45V
TRACK	
EN_LDO, EN_PROT, EN_TRK	0.3V to $(V_{IN} + 0.3V)$
SOURCE	0.3V to $(V_{IN} + 0.3V)$
TRACK to OUT_TRK	40V to +40V
OUT_TRK, FB_TRK, ADJ	5V to +45V
OUT_LDO, FB_LDO, FB_PROT, RESET.	0.3V to +12V
GATE to SOURCE	0.3V to +12V
HOLD0.3	$3V$ to (V_{OUT} LDO + $0.3V$)
REF to SGND	0.3V to +6V
CT to SGND	0.3V to +12V
SGND to PGND	0.3V to +0.3V

IN, OUT_LDO Current	700mA
TRACK, OUT_TRK Current	
Current Sink/Source (all remaining pins)	50mA
Continuous Power Dissipation ($T_A = +70^{\circ}C$))
32-Pin TQFN (derate 34.5mW/°C above +	70°C)2.7W*
Thermal Resistance	
hetaJA	29.0°C/W
θJC	1.7°C/W
Operating Temperature Range	40°C to +125°C
Junction Temperature	
Storage Temperature Range	60°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

^{*}As per JEDEC51 Standard, Multilayer Board (PCB).

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{IN} = V_{TRACK} = +14V, V_{SGND} = V_{PGND} = 0V, C_{GATE} = 6000pF, C_{IN} = 10\mu F (ESR \le 1.5\Omega), C_{OUT_LDO} = 22\mu F (ceramic), C_{TRACK} = 3.3\mu F (ceramic) (ESR \le 1.5\Omega), C_{OUT_TRK} = 10\mu F (ESR \le 1.5\Omega), C_{REF} = 1000pF, V_{OUT_LDO} = 5V, T_A = T_J = -40^{\circ}C to +125^{\circ}C, unless otherwise noted. Typical values are at T_A = +25^{\circ}C.) (Note 1)$

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage Range	VIN			5		40	V
			EN_LDO = IN, EN_TRK = EN_PROT = 0V, IOUT_LDO = 0µA, LDO on, tracker off, protector off, measured from SGND		67	85	
Supply Current	lu.	MAX15008	EN_LDO = EN_TRK = IN, EN_PROT = 0V, LDO on, IOUT_LDO = 100μA, tracker on, IOUT_TRK = 0μA, protector off, VFB_TRK = VOUT_TRK, VADJ = VREF, measured from SGND		120	180	
	liN		EN_LDO = EN_TRK = EN_PROT = IN, LDO on, IOUT_LDO = 100μA, tracker on, IOUT_TRK = 0μA, protector on, VFB_TRK = VOUT_TRK; VADJ = VREF, measured from SGND	190 280 115 160		280	μΑ
		MAX15010	EN_LDO = EN_TRK = IN, LDO on, I _{OUT_LDO} = 100µA, tracker on, I _{OUT_TRK} = 0µA, measured from SGND			160	
Shutdown Supply Current	ISHDN	EN_LDO = EN_PROT = EN TRK = 0V.	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		16	30	μΑ
Gridiadwir dupply durfent	אוטחפי	measured from SGND	$T_A = -40^{\circ}\text{C to } + 125^{\circ}\text{C}$			40	μπ

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = V_{TRACK} = +14V, V_{SGND} = V_{PGND} = 0V, C_{GATE} = 6000pF, C_{IN} = 10\mu F (ESR \le 1.5\Omega), C_{OUT_LDO} = 22\mu F (ceramic), C_{TRACK} = 3.3\mu F (ceramic) (ESR \le 1.5\Omega), C_{OUT_TRK} = 10\mu F (ESR \le 1.5\Omega), C_{REF} = 1000pF, V_{OUT_LDO} = 5V, T_A = T_J = -40^{\circ}C to +125^{\circ}C, unless otherwise noted. Typical values are at <math>T_A = +25^{\circ}C$.) (Note 1)

SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
V _U VLO	V _{IN} falling, GATE disabled	4.10	4.27	4.45	V	
Vuvlo_HYST			260		mV	
REF	I _{REF} = 0µA	1.21	1.235	1.26	V	
I _{REF}	$\Delta V_{REF} = \pm 200 \text{mV}$	-6		+6	μΑ	
T _{SHDN}			+160		°C	
THYST			20		°C	
	I _{LOAD} = 1mA, FB_LDO = SGND	4.92	5	5.09		
V _{OUT_LDO}	I _{LOAD} = 300mA, V _{IN} = 8V, FB_LDO = SGND	4.80	5	5.11	V	
V _{FB_LDO}	With respect to SGND, I _{LOAD} = 1mA, V _{OUT_LDO} = 5V (adjustable output option)	1.21	1.21 1.235 1.26			
M	FB_LDO rising		0.125			
VFB_LDO_TH	FB_LDO falling		0.064		V	
l _{FB_LDO}	V _{FB_LDO} = 1V	-100		+100	nA	
V _{LDO_ADJ}	Adjustable output option (Note 2)	1.8		11.0	V	
\/= a	I _{LOAD} = 300mA		775	1500	mV	
VDO	$I_{LOAD} = 200mA$		520	1000	IIIV	
lout_ldo	(Note 4)	300			mA	
llim_ldo	OUT_LDO = GND, V _{IN} = 6V	330	500	700	mA	
	$6V \le V_{IN} \le 40V$, $I_{LOAD} = 1mA$, $V_{OUT_LDO} = 5V$		0.03	0.2		
Δνουτ/	6V ≤ V _{IN} ≤ 40V, I _{LOAD} = 1mA, V _{OUT_LDO} = 3.3V		0.03	0.1	> (0 (
ΔVIN	6V ≤ V _{IN} ≤ 40V, I _{LOAD} = 20mA, FB_LDO = SGND, V _{OUT_LDO} = 5V		0.27	1	mV/V	
	6V ≤ V _{IN} ≤ 40V, I _{LOAD} = 20mA, V _{OUT_LDO} = 3.3V		0.27	0.5		
ΔV _{OUT} /	1mA to 300mA, V _{IN} = 8V, FB_LDO = SGND, V _{OUT_LDO} = 5V		0.054	0.15		
Δlout	1mA to 300mA, V _{IN} = 6.3V, V _{OUT_LDO} = 3.3V	0.038 0.1			mV/mA	
PSRR	I _{LOAD} = 10mA, f = 100Hz, 500mV _{P-P} , C _{OUT_LDO} = 22μF, V _{OUT_LDO} = 5V		60		dB	
	VUVLO VUVLO_HYST REF IREF TSHDN THYST VOUT_LDO VFB_LDO_TH IFB_LDO VLDO_ADJ VDO IOUT_LDO ILIM_LDO AVOUT/ AVIN AVOUT/ AIOUT	VUVLO VIN falling, GATE disabled VUVLO_HYST REF REF IREF = 0μA IREF ΔVREF = ±200mV TSHDN THYST VOUT_LDO ILOAD = 1mA, FB_LDO = SGND VOUT_LDO ILOAD = 300mA, VIN = 8V, FB_LDO = SGND VFB_LDO With respect to SGND, ILOAD = 1mA, VOUT_LDO = 5V (adjustable output option) FB_LDO rising FB_LDO falling IFB_LDO VFB_LDO = 1V VLDO_ADJ Adjustable output option (Note 2) ILOAD = 300mA ILOAD = 300mA ILOAD = 200mA ILOAD = 200mA ILIM_LDO OUT_LDO = GND, VIN = 6V 6V ≤ VIN ≤ 40V, ILOAD = 1mA, VOUT_LDO = 5V 6V ≤ VIN ≤ 40V, ILOAD = 1mA, VOUT_LDO = 3.3V 6V ≤ VIN ≤ 40V, ILOAD = 20mA, FB_LDO = SGND, VOUT_LDO = 5V 6V ≤ VIN ≤ 40V, ILOAD = 20mA, VOUT_LDO = 3.3V AVOUT/Alout 1mA to 300mA, VIN = 8V, FB_LDO = SGND, VOUT_LDO = 5V 1mA to 300mA, VIN = 6.3V, VOUT_LDO = 3.3V ILOAD = 10mA, f = 100Hz, 500mVP-P,	VUVLO VIN falling, GATE disabled 4.10 VUVLO_HYST	VUVLO VIN falling, GATE disabled 4.10 4.27 VUVLO_HYST 260 REF IREF = 0µA 1.21 1.235 IREF ΔVREF = ±200mV -6 +160 TSHDN +160 +160 THYST 20 ±100 +160 VOUT_LDO ILQAD = 300mA, ViN = 8V, FB_LDO = SGND 4.92 5 ILQAD = 300mA, ViN = 8V, FB_LDO = SGND 4.80 5 VFB_LDO With respect to SGND, ILQAD = 1mA, VOUT_LDO = 5V (adjustable output option) 1.21 1.235 VFB_LDO_TH FB_LDO rising 0.125 0.125 FB_LDO falling 0.04 0.04 IFB_LDO VFB_LDO = 1V -100 VLDO_ADJ Adjustable output option (Note 2) 1.8 VDO ILQAD = 300mA 775 ILOAD = 200mA 520 IOUT_LDO (Note 4) 300 ILIM_LDO OUT_LDO = GND, VIN = 6V 330 500 AVOUT/AVIN 6V ≤ VIN ≤ 40V, ILQAD = 1mA, VOUT_LDO = 5V 0.03 AVOUT/AVIN = 6V ≤ V	VUVLO VIN falling, GATE disabled 4.10 4.27 4.45 VUVLO_HYST 260 260 REF IREF = 0µA 1.21 1.235 1.26 IREF ΔVREF = ±200mV -6 +6 +6 TSHDN +160 +160 +160 TSHDN +160 +160 -160 +160 TSHDN +160 +160 -120 -120 -120 -121 -126 -121 -126 -121 -123 -126 -126 -121 -1235 -126 -126 -126 -126 -126 -126 -126 -126 -126 -126 -126 -126 -126	

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ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = V_{TRACK} = +14V, V_{SGND} = V_{PGND} = 0V, C_{GATE} = 6000pF, C_{IN} = 10\mu F (ESR \le 1.5\Omega), C_{OUT_LDO} = 22\mu F (ceramic), C_{TRACK} = 3.3\mu F (ceramic) (ESR \le 1.5\Omega), C_{OUT_TRK} = 10\mu F (ESR \le 1.5\Omega), C_{REF} = 1000pF, V_{OUT_LDO} = 5V, T_A = T_J = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ unless otherwise noted.}$ Typical values are at $T_A = +25^{\circ}C$.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
OUT_LDO Startup Delay Time	^t STARTUP_DELAY	IOUT_LDO = 0mA, from EN_LDO rising to 10% of VOUT_LDO (nominal), FB_LDO = SGND		30		μs
OUT_LDO Overvoltage Protection Threshold	Vov_th	1mA sink from OUT_LDO		105	110	%Vout_LDO
OUT_LDO Overvoltage Protection Sink Current	lov	Vout_LDO = Vout (nominal) x 1.15	8	19		mA
ENABLE/HOLD INPUTS						
EN_LDO, EN_PROT, EN_TRK Input Threshold	V _{IH}		2			V
Voltage	V _{IL}				0.7	·
EN_LDO, EN_PROT, EN_TRK Input Pulldown Current	I _{EN_PD}	EN_ is internally pulled low to SGND		1		μΑ
HOLD Input Threshold	V _{IH}		1.4			
Voltage	VIL				0.4	V
HOLD Input Pullup	l HOLD _PU	HOLD is internally pulled high to OUT_LDO		0.6		μΑ
RESET						•
RESET Voltage Threshold	V reset h	RESET goes HIGH when rising VOUT_LDO crosses this threshold, FB_LDO = SGND	90.0	92.5	95.0	%Vout_LDO
High	_	RESET goes HIGH when rising VOUT_LDO crosses this threshold	90.0	92.5	95.0	%V _{FB_LDO}
RESET Voltage Threshold	VRESET_L	RESET goes LOW when falling VOUT_LDO crosses this threshold, FB_LDO = SGND	88	90	92	%Vout_LDO
Low		RESET goes LOW when falling VOUT_LDO crosses this threshold	88	90	92	%V _{FB_LDO}
V _{OUT_LDO} to RESET Delay	^t RESET_FALL	V _{OUT_LDO} falling, 0.1V/µs		19		μs
CT Ramp Current	ICT	$V_{CT} = 0V$	1.50	2.0	2.35	μΑ
CT Ramp Threshold	V _{CT_TH}	V _{CT} rising	1.19	1.235	1.27	V
RESET Output-Voltage Low	V _{OL}	Isink = 1mA, output asserted			0.1	V
RESET Open-Drain Leakage Current	I _{LEAK_RESET}	Output not asserted			150	nA
LOAD DUMP PROTECTOR	(MAX15008 only)					•
FB_PROT Threshold Voltage	VTH_PROT	FB_PROT rising	1.20	1.235	1.27	V
FB_PROT Threshold Hysteresis	VHYST			4		%V _{TH_PROT}
FB_PROT Input Current	I _{FB_PROT}	VFB_PROT = 1.4V	-100		+100	nA
Startup Response Time	tstart	EN_PROT rising, EN_LDO = IN, to VGATE = 0.5V		20		μs

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ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = V_{TRACK} = +14V, V_{SGND} = V_{PGND} = 0V, C_{GATE} = 6000pF, C_{IN} = 10\mu F (ESR \le 1.5\Omega), C_{OUT_LDO} = 22\mu F (ceramic), C_{TRACK} = 3.3\mu F (ceramic) (ESR \le 1.5\Omega), C_{OUT_TRK} = 10\mu F (ESR \le 1.5\Omega), C_{REF} = 1000pF, V_{OUT_LDO} = 5V, T_A = T_J = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ unless otherwise noted.}$ Typical values are at $T_A = +25^{\circ}C.$) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
GATE Rise Time	tgate	GATE rising to +8V, VSOURCE = 0V		1		ms
FB_PROT to GATE Turn-Off Propagation Delay	tov	FB_PROT step from V _{TH_PROT} - 250mV to V _{TH_PROT} + 250mV			0.6	μs
CATE Output High Voltage	\/	$\begin{aligned} &\text{V}_{\text{SOURCE}} = \text{V}_{\text{IN}} = 5.5\text{V}, \\ &\text{R}_{\text{GATE}} \text{ to IN} = 1\text{M}\Omega \end{aligned}$	IN + 3.2	IN + 3.5	IN + 3.8	V
GATE Output High Voltage	VGATE	$\begin{aligned} &V_{SOURCE} = V_{IN}; V_{IN} \geq 14V, \\ &R_{GATE} \text{ to IN} = 1\text{M}\Omega \end{aligned}$	IN + 7.0	IN + 8.1	IN + 9.5	V
GATE Output Pulldown Current	IGATEPD	VGATE = 5V, VEN_PROT = 0V		63	100	mA
GATE Charge-Pump Current	IGATE	GATE = SGND		45		μΑ
GATE-to-SOURCE Clamp Voltage	V _{CLMP}		12	16	18	V
TRACKER						
Tracker Supply Voltage Range	VTRACK		5		40	V
ADJ, FB_TRK Input Voltage	V _{ADJ} , V _{FB_TRK}		1.1		TRACK - 0.5	V
Tracker Output Common- Mode Range	Vсм		1.1		TRACK - 0.5	V
Tracking Accuracy Over Line	ΔVQ_LINE	IOUT_LDO = 20mA, VFB_TRK = VOUT_TRK = 5V, VTRACK = 6V to 28V, ΔVQ = VFB_TRK - VADJ	-3		+3	mV
Tracking Accuracy Over Load	ΔVQ_LOAD	VTRACK = 6V, 0.1mA \leq I _{OUT_TRK} \leq 50mA, V _{ADJ} = V _{OUT_TRK} = 5V, Δ VQ = VFB_TRK - VADJ	-3		+3	mV
ADJ, FB_TRK Input Current	IFB_TRK, IADJ	V _{FB_TRK} = V _{ADJ} = 5V		0.03	0.2	μΑ
Dropout Voltage	V_{DO}	V _{OUT_TRK} = 5V, I _{OUT_TRK} = 50mA		0.28	0.5	V
Tracker Output Current	I _{OUT_TRK}	VADJ = VOUT_TRK = 5V	50			mA
Output Current Limit	IOUT_TRK_LIM	Vout_trk = 0V	85	100	115	mA
Current Consumption	IQ	IQ = ITRACK - IOUT_TRK, IOUT_TRK = 50mA, VADJ = VFB_TRK = 5V, EN_LDO = EN_PROT = SGND, EN_TRK = IN		2.7	6	mA
OUT_TRK Power-Supply Rejection Ratio	PSRR	IOUT_LDO = 10mA, f = 100Hz, 500mVp-p, VOUT_TRK = VFB_TRK, VADJ = 5V		60		dB
OUT_TRK Reverse Current	lout_trk_reverse	VTRACK = 14V, VOUT_TRK = VFB_TRK = 40V, V _{ADJ} = 5V	_	10		μΑ

Note 1: Limits to -40°C are guaranteed by design.

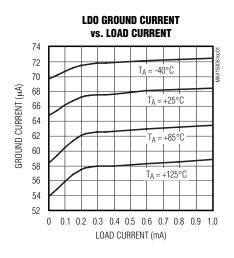
Note 2: 1.8V is the minimum limit for proper HOLD functionality.

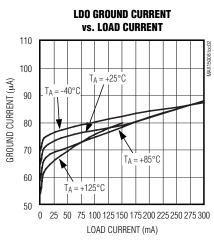
Note 3: Dropout is defined as V_{IN} - V_{OUT_LDO} when V_{OUT_LDO} is 98% of the value of V_{OUT_LDO} for $V_{IN} = V_{OUT_LDO} + 1.5V$.

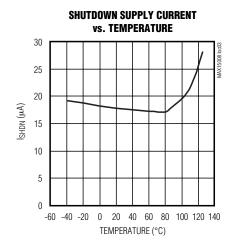
Note 4: Maximum output current may be limited by the power dissipation of the package.

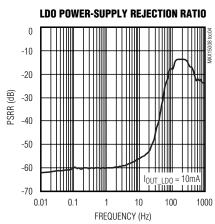
Typical Operating Characteristics

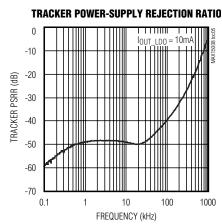
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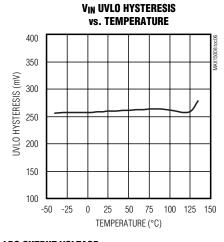


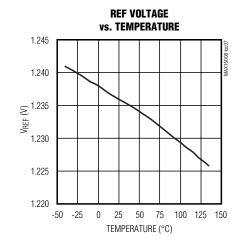


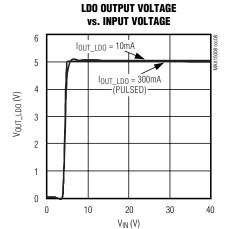






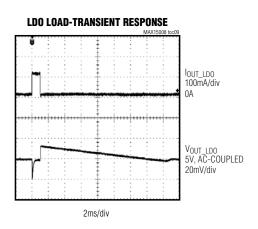


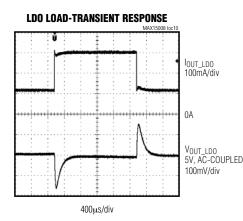


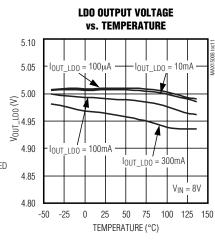


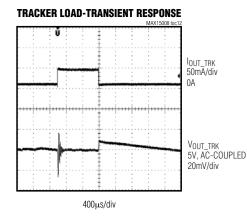
Typical Operating Characteristics (continued)

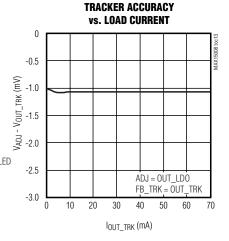
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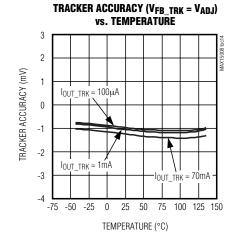


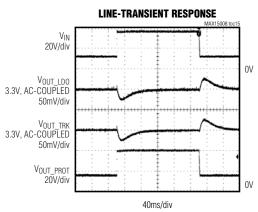


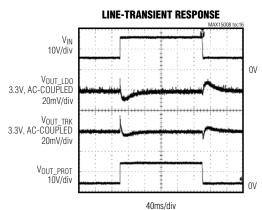






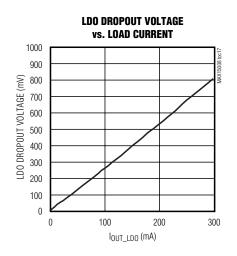


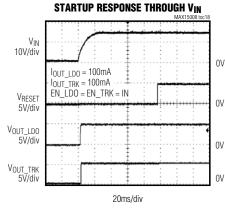


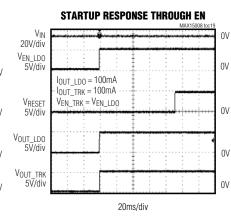


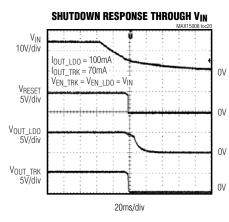
Typical Operating Characteristics (continued)

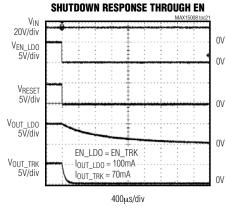
 $(V_{IN} = V_{EN_} = +14V, C_{IN} = 10\mu\text{F}, C_{OUT_LDO} = 22\mu\text{F}, C_{TRACK} = C_{OUT_TRK} = 10\mu\text{F}, V_{OUT_LDO} = 5V, FB_LDO = SGND, T_A = +25^{\circ}\text{C}, unless otherwise specified.)$

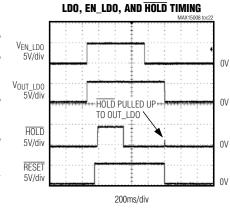


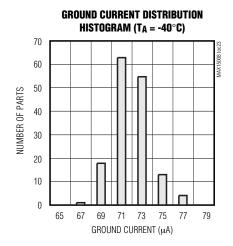


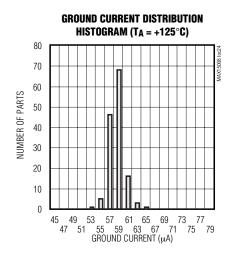






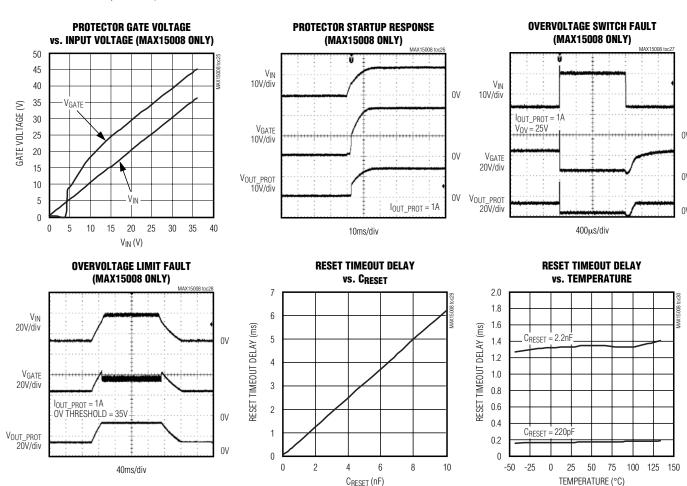






Typical Operating Characteristics (continued)

 $(V_{IN} = V_{EN} = +14V, C_{IN} = 10\mu\text{F}, C_{OUT_LDO} = 22\mu\text{F}, C_{TRACK} = C_{OUT_TRK} = 10\mu\text{F}, V_{OUT_LDO} = 5V, FB_LDO = SGND, T_A = +25^{\circ}\text{C}, unless otherwise specified.)$



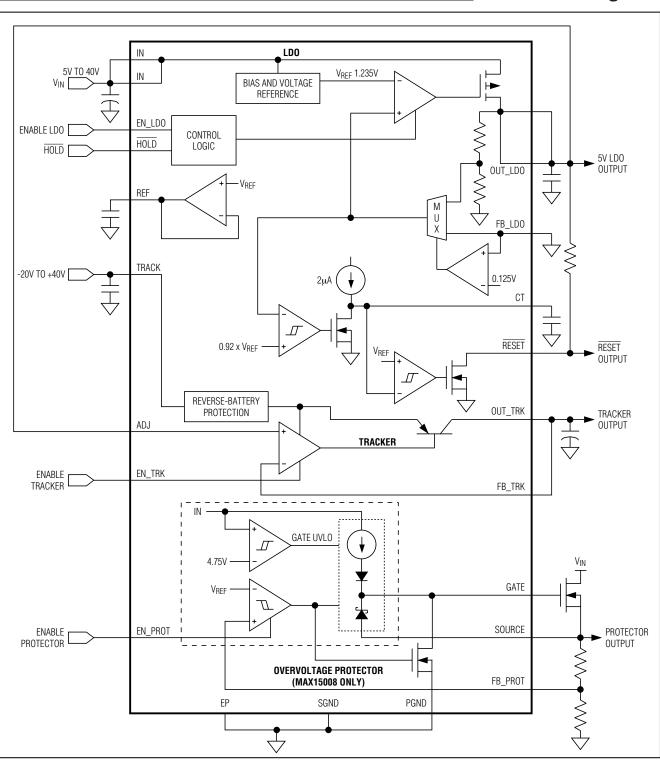
Pin Description

PI	IN	NAME	FUNCTION
MAX15008	MAX15010	NAME	FUNCTION
1, 2, 8, 11, 23, 24, 26, 27, 28, 31, 32	1, 2, 8, 10–13, 18, 23, 24, 26, 27, 28, 31, 32	N.C.	No Connection. Not internally connected.
3	3	OUT_TRK	Tracker Output. Bypass OUT_TRK to SGND with a 10µF (min) capacitor with low ESR (\leq 1.5 Ω).
4	4	ADJ	Tracker Amplifier Input. Connect ADJ to OUT_LDO or to an external source to track. Alternatively, connect ADJ to REF to provide the reference voltage to the tracker.
5	5	SGND	Signal Ground
6	6	PGND	Ground. PGND is also the return path for the overvoltage protector pulldown current for the MAX15008. In this case, connect PGND to SGND at the negative terminal of the bypass capacitor connected to the source of the external MOSFET. For the MAX15010, connect PGND to SGND together to the local ground plane.
7	7	RESET	Active-Low Open-Drain Reset Output. RESET is low while OUT_LDO is below the reset threshold. Once OUT_LDO has exceeded the reset threshold, RESET remains low for the duration of the reset timeout period before going high.
9	9	СТ	Reset Timeout Adjust Input. Connect a capacitor (C _{RESET}) from CT to ground to adjust the reset timeout period. See the Setting the RESET Timeout Period section.
10		FB_PROT	Overvoltage Threshold Adjustment Input. Connect FB_PROT to an external resistive voltage-divider network to adjust the desired overvoltage threshold. Use FB_PROT to monitor a system input or output voltage. See the Setting the Overvoltage Threshold (MAX15008 Only) section.
12	_	GATE	Protector Gate Drive Output. Connect GATE to the gate of an external n-channel MOSFET. GATE is the output of a charge pump with a 45µA pullup current to 7.1V (typ) above IN during normal operation. GATE is quickly turned off through a 63mA internal pulldown during an overvoltage condition. GATE then remains low until FB_PROT has decreased 96% below the threshold. GATE pulls low when EN_PROT is low.
13	_	SOURCE	Output-Voltage Sense Input. Connect SOURCE to the source of the external n-channel MOSFET.
14	14	REF	1.235V Voltage Reference Output. Bypass REF to SGND with a 1nF or larger capacitor.

Pin Description (continued)

PIN			
MAX15008	MAX15010	NAME	FUNCTION
15	15	FB_LDO	LDO Voltage Feedback Input. Connect FB_LDO to SGND to select the preset +5V output voltage. Connect FB_LDO to an external resistive voltage-divider for adjustable output operation. See the Setting the Output Voltage section.
16	16	EN_LDO	Active-High LDO Enable Input. Connect EN_LDO to IN or to a logic-high voltage to turn on the regulator. To place the LDO in shutdown, pull EN_LDO low or leave unconnected and leave HOLD unconnected. EN_LDO is internally pulled to SGND through a 1µA current sink. See the <i>Control Logic</i> section.
17	17	EN_TRK	Active-High Tracker Enable Input. Connect EN_TRK to IN or to a logic-high voltage to turn on the tracker. Pull EN_TRK low or leave unconnected to place tracker in shutdown. EN_TRK is internally pulled to SGND through a 1µA current sink.
18	_	EN_PROT	Protector Enable Input. Drive EN_PROT low to force GATE low and turn off the external n-channel MOSFET. EN_PROT is internally pulled to SGND by a 1µA sink. Connect EN_PROT to IN for normal operation.
19, 20	19, 20	IN	Regulator Input. Bypass IN to SGND with a 10μF capacitor (ESR ≤ 1.5Ω).
21, 22	21, 22	OUT_LDO	LDO Regulator Output. Bypass OUT_LDO to SGND with a low-ESR capacitor with a minimum value of 22µF. Fixed +5V or adjustable output (+1.8V to +11V). See the Setting the Output Voltage section.
25	25	HOLD	Active-Low Hold Input. If EN_LDO is high when HOLD is forced low, the regulator latches the state of the EN_LDO input and allows the regulator to remain turned on when EN_LDO is subsequently pulled low. To shut down the regulator, release HOLD after EN_LDO is pulled low. If HOLD functionality is unused, connect HOLD to OUT_LDO or leave unconnected. HOLD is internally pulled up to OUT_LDO through a 0.6µA current source. See the <i>Control Logic</i> section.
29	29	FB_TRK	Tracker Amplifier Feedback. Connect FB_TRK directly to OUT_TRK or through an external resistive voltage-divider.
30	30	TRACK	Tracker Input. Bypass TRACK to the SGND with a 3.3µF ceramic capacitor.
EP	EP	EP	Exposed Pad. Connect EP to SGND plane. EP also functions as a heatsink to maximize thermal dissipation. Do not use as the main ground connection.





Detailed Description

The MAX15008/MAX15010 integrate a 300mA LDO voltage regulator, a voltage tracker, and an OVP controller. These devices operate over a wide 5V to 40V supply voltage range and are able to withstand load-dump transients up to 45V.

The MAX15008/MAX15010 feature a 300mA LDO regulator that consumes less than $70\mu A$ of current under light-load conditions and feature a fixed 5V or an adjustable output voltage (1.8V to 11V). Connect FB_LDO to ground to select a fixed 5V output voltage or select the LDO output voltage by connecting an external resistive voltage-divider at FB_LDO. The regulator sources at least 300mA of current and includes a current limit of 330mA (min). Enable the LDO by pulling EN_LDO high.

The tracker can be powered from the LDO input supply voltage or an independent voltage source. It is designed to supply power to a remote sensor and is able to handle the severe conditions in automotive applications. Set the tracker output voltage by connecting a resistive voltage-divider to OUT_TRK and connecting ADJ to the tracking source. The tracker feedback, FB_TRK, and a separate tracker reference voltage input, ADJ, offer the flexibility of setting the tracker output to be lower, equal to, or higher than the main (LDO) output. Pull EN_TRK to SGND to turn the tracker off and keep the device in always-on, low-quiescent-current operation.

The OVP controller (MAX15008 only) relies on an external MOSFET with adequate voltage rating (VDSS) to protect downstream circuitry from overvoltage transients. The OVP controller drives the gate of the external n-channel MOSFET, and is configurable to operate as an overvoltage protection switch or as a closed-loop voltage limiter.

GATE Voltage (MAX15008 Only)

The MAX15008 uses a high-efficiency charge pump to generate the GATE voltage for the external n-channel MOSFET. Once the input voltage, V_{IN}, exceeds the undervoltage lockout (UVLO) threshold, the internal charge pump fully enhances the external n-channel MOSFET. An overvoltage condition occurs when the voltage at FB_PROT goes above the threshold voltage, V_{TH_PROT}. After V_{TH_PROT} is exceeded, GATE is quickly pulled to PGND with a 63mA pulldown current. The MAX15008 includes an internal clamp from GATE to SOURCE that ensures that the voltage at GATE never exceeds one diode drop below SOURCE during gate

discharge. The voltage clamp also prevents the GATE-to-SOURCE voltage from exceeding the absolute maximum rating for the VGS of the external MOSFET in case the source terminal is accidentally shorted to 0V.

Overvoltage Monitoring (MAX15008 Only)

The OVP controller monitors the voltage at FB_PROT and controls an external n-channel MOSFET, isolating, or limiting the load during an overvoltage condition. Operation in OVP switch mode or limiter mode depends on the connection between FB_PROT and the external MOSFET.

Overvoltage Switch Mode

When operating in OVP switch mode, the FB_PROT divider is connected to the drain of the external MOSFET. The feedback path consists of the voltage-divider tapped at FB_PROT, FB_PROT's internal comparator, the internal gate charge pump/gate pulldown, and the external n-channel MOSFET (Figure 1). When the programmed overvoltage threshold is exceeded, the internal comparator quickly pulls GATE to ground and turns off the external MOSFET, disconnecting the power source from the load. In this configuration, the voltage at the source of the MOSFET is not monitored. When the voltage at FB_PROT decreases below the overvoltage threshold, the MAX15008 raises the voltage at GATE, reconnecting the load to the power source.

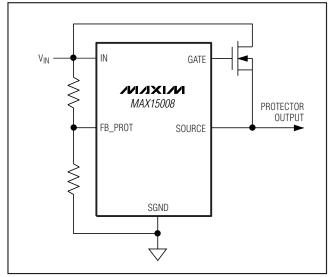


Figure 1. Overvoltage Switch Configuration (MAX15008)

Overvoltage-Limiter Mode

When operating in overvoltage-limiter mode, the feedback path consists of SOURCE, FB_PROT's internal comparator, the internal gate charge pump/gate pull-down, and the external n-channel MOSFET (Figure 2). This configuration results in the external MOSFET operating as a hysteretic voltage regulator.

During normal operation, GATE is enhanced 8.1V above VIN. The external MOSFET source voltage is monitored through a resistive voltage-divider between SOURCE and FB_PROT. When Vsource exceeds the adjustable overvoltage threshold, an internal pulldown switch discharges the gate voltage and quickly turns the MOSFET off. Consequently, the source voltage begins to fall. The V_{SOURCE} fall time is dependent on the MOSFET's gate charge, the internal charge-pump current, the output load, and any load capacitance at SOURCE. When the voltage at FB_PROT is below the overvoltage threshold by an amount equal to the hysteresis, the charge pump restarts and turns the MOSFET back on. In this way, the OVP controller attempts to regulate VSOURCE around the overvoltage threshold. SOURCE remains high during overvoltage transients and the MOSFET continues to conduct during an overvoltage event. The hysteresis of the FB_PROT comparator and the gate turn-on delay force the external MOSFET to operate in a switched on/off sequence during an overvoltage event.

Exercise caution when operating the MAX15008 in voltage-limiting mode for long durations. Care must be taken against prolonged or repeated exposure to overvoltage events while delivering large amounts of load current as the power dissipation in the external MOSFET may be high under these conditions. To prevent damage to the MOSFET, implement proper heatsinking. The capacitor connected between SOURCE and ground can also be damaged if the ripple current rating for the capacitor is exceeded.

As the transient voltage decreases, the voltage at SOURCE falls. For fast-rising transients and very large MOSFETs, connect an additional capacitor from GATE to PGND. This capacitor acts as a voltage-divider work-

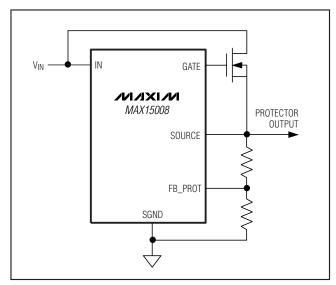


Figure 2. Overvoltage Limiter (MAX15008)

ing against the MOSFET's drain-to-gate capacitance. If using a very low gate charge MOSFET, additional capacitance from GATE to ground might be required to reduce the switching frequency.

Control Logic

The MAX15008/MAX15010 LDO features two logic inputs, EN_LDO and HOLD, making these devices suitable for automotive applications. For example, when the ignition key signal drives EN_LDO high, the regulator turns on and remains on even if EN_LDO goes low, as long as HOLD is forced low and stays low after initial regulator power-up. In this state, releasing HOLD turns the regulator output (OUT_LDO) off. This feature makes it possible to implement a self-holding circuit without external components. Forcing EN_LDO low and HOLD high (or unconnected) places the regulator into shutdown mode reducing the supply current to less than 16μA. Table 1 shows the state of OUT_LDO with respect to EN_LDO and HOLD. Leave HOLD unconnected or connect directly to OUT_LDO to allow the EN_LDO input to act as a standard on/off logic input for the regulator.

Table 1. EN_LDO/HOLD Truth Table/State Table

OPERATION STATE	EN_LDO	HOLD	OUT_LDO	COMMENT
Initial State	Low	Don't care	OFF	EN_LDO is pulled to SGND through an internal pulldown. HOLD is unconnected and is internally pulled up to OUT_LDO. The regulator is disabled.
Turn-On State	High	Don't care	ON	EN_LDO is externally driven high turning regulator on. HOLD is pulled up to OUT_LDO.
Hold Setup State	High	Low	ON	HOLD is externally pulled low while EN_LDO remains high (latches EN_LDO state).
Hold State	Low	Low	ON	EN_LDO is driven low or left unconnected. HOLD remains externally pulled low keeping the regulator on.
Off State	Low	High or unconnected	OFF	HOLD is driven high or left unconnected while EN_LDO is low. The regulator is turned off and EN_LDO/HOLD logic returns to the initial state.

Applications Information

Load Dump

Most automotive applications run off a multicell 12V lead-acid battery with a nominal voltage that swings between 9V and 16V, depending on load current. charging status, temperature, and battery age, etc. The battery voltage is distributed throughout the automobile and is locally regulated down to voltages required by the different system modules. Load dump occurs when the alternator is charging the battery and the battery becomes disconnected. Power in the alternator (behaving now essentially as an inductor) flows into the distributed power system and elevates the voltage seen at each module. The voltage spikes have rise times typically greater than 5ms and decay within several hundred milliseconds but can extend out to 1s or more depending on the characteristics of the charging system. These transients are capable of destroying semiconductors on the first fault event.

The MAX15008/MAX15010 feature load-dump transient protection up to +45V.

Setting the Output Voltage

The MAX15008/MAX15010 feature dual-mode operation: these devices operate in either a preset voltage mode or an adjustable mode. In preset voltage mode, internal feedback resistors set the linear regulator out-

put voltage (V_{OUT_LDO}) to 5V. To select the preset 5V output voltage, connect FB_LDO to SGND.

To select an adjustable output voltage between 1.8V and 11V, use two external resistors connected as a voltage-divider to FB_LDO (Figure 3). Set the output voltage using the following equation:

 $V_{OUT_LDO} = V_{FB_LDO} ~x~(R_1 + R_2) ~/~R_2$ where $V_{FB_LDO} = 1.235 V$ and $R_2 \le 50 k \Omega.$

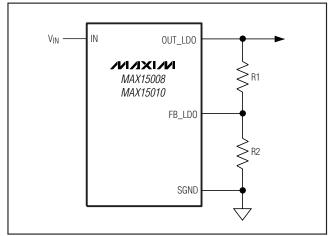


Figure 3. Setting the LDO Output Voltage

Setting the RESET Timeout Period

The reset timeout period is adjustable to accommodate a variety of applications. Set the reset timeout period by connecting a capacitor, CRESET, between CT and SGND. Use the following formula to select the reset timeout period, tRESET:

treset = Creset x Vct_th / Ict

where treset is in seconds and Creset is in μ F. VCT_TH is the CT ramp threshold in volts and ICT is the CT ramp current in μ A, as described in the *Electrical Characteristics* table.

Leave CT open to select an internally fixed timeout period of 10µs. To maintain reset timeout accuracy, use a low-leakage (< 10nA) type capacitor.

Tracker Input/Feedback Adjustment

The tracker can be powered from the LDO input supply voltage or an independent voltage source. It is designed to supply power to a remote sensor and its supply input, TRACK, is able to handle the severe conditions in automotive applications such as battery reversal and load-dump transients up to 45V.

The tracker feedback, FB_TRK, and a separate tracker reference voltage input, ADJ, offer the flexibility of set-

ting the tracker output to be lower, equal to, or higher than the main (LDO) output. Other external voltages can also be tracked.

Connect ADJ to OUT_LDO and FB_TRK to OUT_TRK to track the LDO output voltage directly (Figure 4a). To track a voltage higher than VOUT_LDO, directly connect ADJ to OUT_LDO and connect FB_TRK to OUT_TRK through a resistive voltage-divider (Figure 4b). To track a voltage lower than the LDO regulator output, VOUT_LDO, directly connect FB_TRK to OUT_TRK and connect ADJ to OUT_LDO through a resistive voltage-divider (Figure 4c). To track an external voltage Vx with a generic attenuation/amplification ratio, connect resistive voltage-dividers between ADJ and the voltage input or output to be tracked (Vx), and between OUT_TRK and FB_TRK (Figure 4d). Pay attention to the resistive loading of the voltage Vx due to the divider R5, R6.

To track the internal REF voltage (1.235V), directly connect ADJ to REF. The voltage at FB_TRK or ADJ should be greater than or equal to 1.1V and less than V_{TRACK} - 0.5V. Resistors should have a tolerance of 1% or better. Their values should be low enough to ensure that the divider current is at least 100x the maximum input bias current at pins FB_TRK and ADJ (IFB_TRK_ADJ, max = 0.2 μ A).

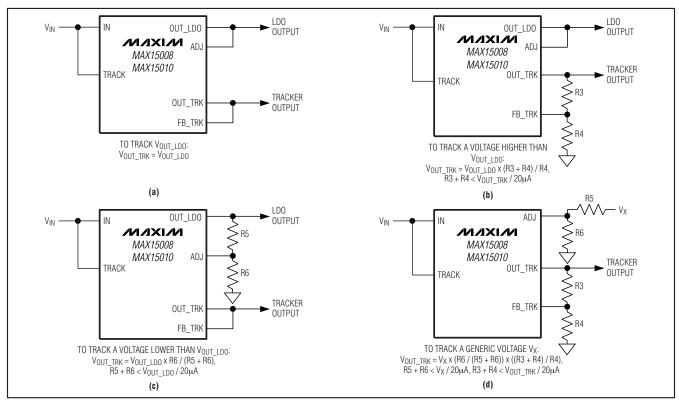


Figure 4. Tracker Input and Feedback Adjustment

Setting the Overvoltage Threshold (MAX15008 Only)

The MAX15008 provides an accurate means to set the overvoltage threshold for the OVP controller using FB_PROT. Use a resistive voltage-divider to set the desired overvoltage threshold (Figure 5). FB_PROT has a rising 1.235V threshold with a 4% falling hysteresis.

Begin by selecting the total end-to-end resistance, RTOTAL = R5 + R6. Choose RTOTAL to yield a total current equivalent to a minimum of 100 x IFB_PROT (FB_PROT's input maximum bias current) at the desired overvoltage threshold. See the *Electrical Characteristics* table.

For example:

With an overvoltage threshold (Vov) set to 20V, RTOTAL < 20V / (100 x IFB_PROT), where IFB_PROT is FB_PROT's maximum 100nA bias current:

RTOTAL $< 2M\Omega$

Use the following formula to calculate R₆:

where V_{TH_PROT} is the 1.235V FB_PROT rising threshold and V_{OV} is the desired overvoltage threshold. $R_6 = 124k\Omega$:

$$RTOTAL = R_5 + R_6$$

where $R_5 = 1.88M\Omega$. Use a standard $1.87M\Omega$ resistor.

A lower value for total resistance dissipates more power, but provides better accuracy and robustness against external disturbances.

Input Transients Clamping

When the external MOSFET is turned off during an overvoltage event, stray inductance in the power path may cause additional input-voltage spikes that exceed the VDSS rating of the external MOSFET or the absolute maximum rating for the MAX15008 (IN, TRACK). Minimize stray inductance in the power path using wide traces and minimize the loop area included by the power traces and the return ground path.

For further protection, add a zener diode or transient voltage suppressor (TVS) rated below the absolute maximum rating limits (Figure 6).

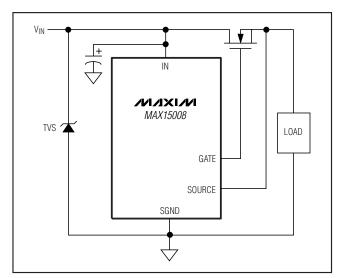


Figure 6. Protecting the MAX15008 Input from High-Voltage Transients

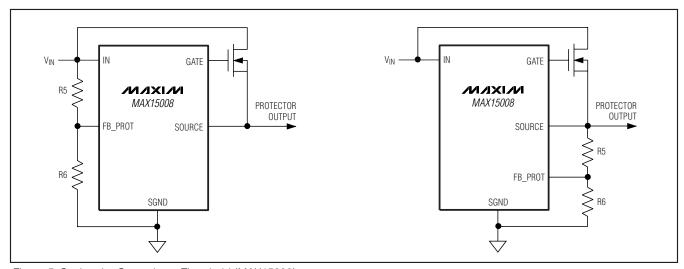


Figure 5. Setting the Overvoltage Threshold (MAX15008)

External MOSFET Selection

Select the external MOSFET with adequate voltage rating, V_{DSS}, to withstand the maximum expected load-dump input voltage. The on-resistance of the MOSFET, R_{DS(ON)}, should be low enough to maintain a minimal voltage drop at full load, limiting the power dissipation of the MOSFET.

During regular operation, the power dissipated by the MOSFET is:

$$PNORMAL = ILOAD^2 \times RDS(ON)$$

Normally, this power loss is small and is safely handled by the MOSFET. However, when operating the MAX15008 in overvoltage-limiter mode under prolonged or frequent overvoltage events, select an external MOSFET with an appropriate power rating.

During an overvoltage event, the power dissipation in the external MOSFET is proportional to both load current and to the drain-source voltage, resulting in high power dissipated in the MOSFET (Figure 7). The power dissipated across the MOSFET is:

where V_{Q1} is the voltage across the MOSFET's drain and source during overvoltage-limiter operation, and $I_{I,QAD}$ is the load current.

Overvoltage-Limiter Mode Switching Frequency

When the MAX15008 is configured in overvoltagelimiter mode, the external n-channel MOSFET is subse-

VSOURCE

VSO

Figure 7. Power Dissipated Across MOSFETs During an Overvoltage Fault (Overvoltage Limiter Mode)

quently switched on and off during an overvoltage event. The output voltage at SOURCE resembles a periodic sawtooth waveform. Calculate the period of the waveform, tovp, by summing three time intervals (Figure 8):

$$tOVP = t_1 + t_2 + t_3$$

where t₁ is the V_{SOURCE} output discharge time, t₂ is the GATE delay time, and t₃ is the V_{SOURCE} output charge time.

During an overvoltage event, the power dissipated inside the MAX15008 is due to the gate pulldown current, IGATEPD. This amount of power dissipation is worse when ISOURCE = 0 (CSOURCE is discharged only by the internal current sink).

The worst-case internal power dissipation contribution in overvoltage-limiter mode, POVP, in watts can be approximated using the following equation:

$$P_{OVP} = V_{OV} \times 0.98 \times I_{GATEPD} \times \frac{t_1}{t_{OVP}}$$

where V_{OV} is the overvoltage threshold voltage in volts and I_{GATEPD} is the 63mA (typ) GATE pulldown current.

Output Discharge Time (t₁)

When the voltage at SOURCE exceeds the adjusted overvoltage threshold, GATE's internal pulldown is enabled until VSOURCE drops by 4%. The internal current sink, IGATEPD, and the external load current, ILOAD, discharge the external capacitance from SOURCE to ground.

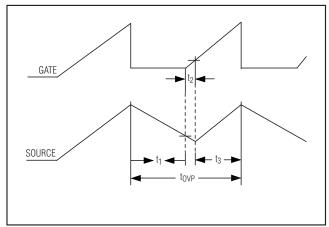


Figure 8. MAX15008 Timing Diagram

Calculate the discharge time, t₁, using the following equation:

$$t_1 = C_{SOURCE} \times \frac{0.04 \times V_{OV}}{I_{LOAD} + I_{GATEPD}}$$

where t_1 is in ms, Vov is the adjusted overvoltage threshold in volts, I_{LOAD} is the external load current in mA, and I_{GATEPD} is the 63mA (typ) internal pulldown current of GATE. CSOURCE is the value of the capacitor connected between the source of the MOSFET and PGND in μF .

GATE Delay Time (t₂)

When SOURCE falls 4% below the overvoltage threshold voltage, the internal current sink is disabled and the internal charge pump begins recharging the external GATE voltage. Due to the external load, the SOURCE voltage continues to drop until the gate of the MOSFET is recharged. The time needed to recharge GATE and reenhance the external MOSFET is approximately:

$$t_2 = C_{iss} \times \frac{V_{GS(TH)} + V_F}{I_{GATE}}$$

where t₂ is in μ s, C_{iSS} is the input capacitance of the MOSFET in pF, and $V_{GS(TH)}$ is the gate-to-source threshold voltage of the MOSFET in volts. VF is the 0.7V (typ) internal clamp diode forward voltage of the MOSFET in volts, and I_{GATE} is the charge-pump current 45 μ A (typ). Any external capacitance between GATE and PGND will add up to C_{iss} .

During t₂, the SOURCE capacitance, C_{SOURCE}, loses charge through the output load. The voltage across C_{SOURCE} decreases by ΔV_2 until the MOSFET reaches its V_{GS(TH)} threshold. Approximate ΔV_2 using the following formula:

$$\Delta V_2 = \frac{I_{LOAD} \times t_2}{C_{SOURCE}}$$

SOURCE Output Charge Time (t3)

Once the GATE voltage exceeds the gate-to-source threshold, VGS(TH), of the external MOSFET, the MOSFET turns on and the charge through the internal charge pump with respect to the drain potential, QG, determines the slope of the output-voltage rise. The time required for the SOURCE voltage to rise again to the overvoltage threshold is:

$$t_3 = \frac{C_{rss} \times \Delta V_{SOURCE}}{I_{GATE}}$$

where $\Delta V_{SOURCE} = (V_{OV} \times 0.04) + \Delta V_2$ in volts, and C_{rss} is the MOSFET's reverse transfer capacitance in pF. Any external capacitance between GATE and PGND adds up to C_{rss} .

Power Dissipation/Junction Temperature

During normal operation, the MAX15008/MAX15010 has two main sources of internal power dissipation: the LDO and the voltage tracker.

Calculate the power dissipation due to the LDO as:

where V_{IN} is the LDO input supply voltage in volts, V_{OUT_LDO} is the output voltage of the LDO in volts, and I_{OUT_LDO} is the LDO total load current in mA.

Calculate power dissipation due to the tracker as:

where VTRACK is the tracker input supply voltage in volts, VOUT_TRK is the output voltage of the tracker in volts, and IOUT_TRK is the tracker load current in mA.

The total power dissipation PDISS in mW as:

For prolonged exposure to overvoltage events, use the V_{IN} and V_{TRACK} voltages expected during overvoltage conditions. Under these circumstances the corresponding internal power dissipation contribution, P_{OVP}, calculated in the *Overvoltage-Limiter Mode Switching Frequency* section should also be included in the total power dissipation, P_{DISS}.

For a given ambient temperature, T_A, calculate the junction temperature, T_J, as follows:

$$T_J = T_A + P_{DISS} \times \theta_{JA}$$

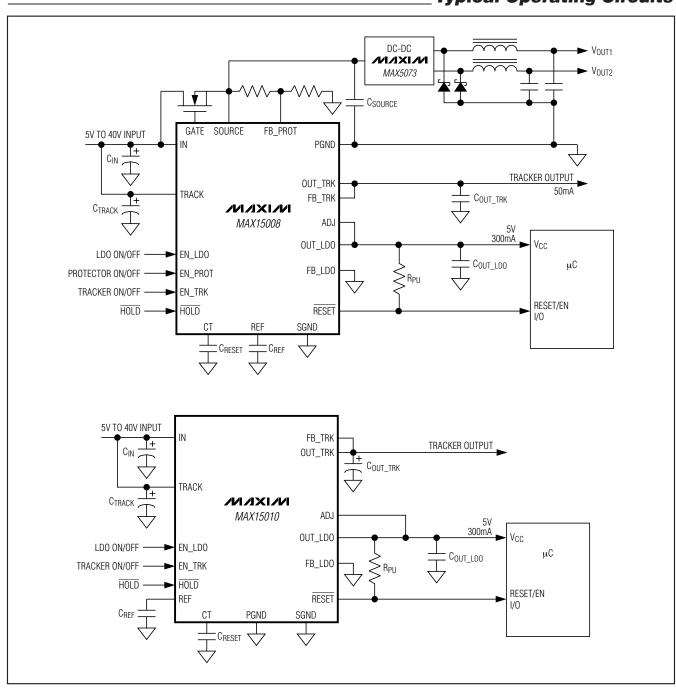
where T_J and T_A are in °C and θ_{JA} is the junction-to-ambient thermal resistance in °C/W as listed in the *Absolute Maximum Ratings* section.

The junction temperature should never exceed +150°C during normal operation.

Thermal Protection

When the junction temperature exceeds $T_J = +160^{\circ}C$, the MAX15008/MAX15010 shut down to allow the device to cool. When the junction temperature drops to $+140^{\circ}C$, the thermal sensor turns all enabled blocks on again, resulting in a cycled output during continuous thermal-overload conditions. Thermal protection protects the MAX15008/MAX15010 from excessive power dissipation. For continuous operation, do not exceed the absolute maximum junction temperature rating of $+150^{\circ}C$.

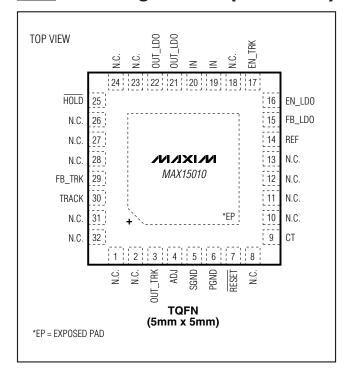




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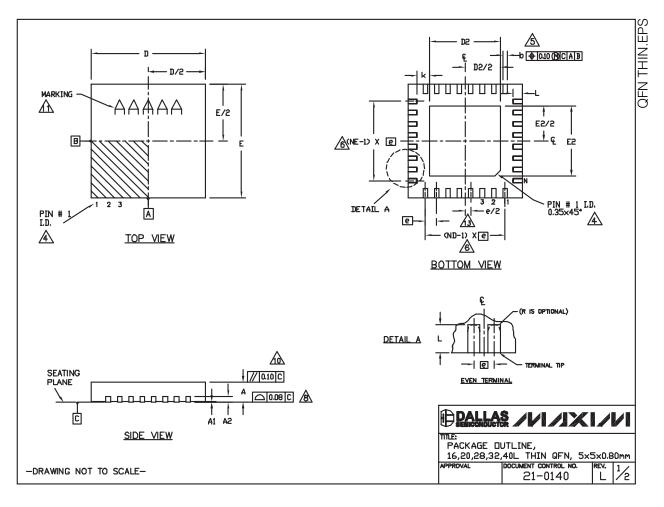
Pin Configurations (continued)

_____**Chip Information**PROCESS: BICMOS



Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages.)



Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages.)

COMMON DIMENSIONS															
PKG.	16	L 5	×5	2	DL 5	5×5	2	28L 5x5		38	2L 5	5×5	41	40L 5×5	
SYMBOL	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.	MIN.	NOM.	MAX.
Α	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80
A1	0	0.02	0.05	0	0.02	0.05	0	0.02	0.05	0	0.02	0.05	٥	0.02	0.05
A2	0.8	20 RE	F.	0.7	20 RE	F.	0.2	20 RE	F.	0.2	20 RE	F.	0.8	20 RE	F.
b	0.25	0.30	0.35	0.25	0.30	0.35	0.20	0.25	0.30	0.20	0.25	0.30	0.15	0.20	0.25
D	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10
E	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10
e	0.	80 B	SC.	0.65 BSC.		0.50 BSC.		0.50 BSC.		0.40 BSC.					
ĸ	0.25	-	-	0.25	1	-	0.25	-	-	0.25	-	-	0.25	ı	-
L	0.30	0.40	0.50	0.45	0.55	0.65	0.45	0.55	0.65	0.30	0.40	0.50	0.30	0.40	0.50
N		16			20			28		32			40		
ND		4			5			7		8		10			
NE		4			5			7		8			10		
JEDEC		WHHB		1	WHHC		\ \	/HHD-	-1	VHHD-2					

ΝП	TE C.	

- 1. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
- ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
- N IS THE TOTAL NUMBER OF TERMINALS.
- THE TERMINAL #1 IDENTIFIER AND TERMINAL NUMBERING CONVENTION SHALL CONFORM TO JESD 95-1 SPP-012. DETAILS OF TERMINAL #1 IDENTIFIER ARE OPTIONAL, BUT MUST BE LOCATED WITHIN THE ZONE INDICATED. THE TERMINAL #1 IDENTIFIER MAY BE EITHER A MOLD OR MARKED FEATURE.
- ⚠ DIMENSION 6 APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.25 mm AND 0.30 mm FROM TERMINAL TIP.
- riangle ND and NE refer to the number of terminals on each D and E side respectively.
- DEPOPULATION IS POSSIBLE IN A SYMMETRICAL FASHION.
- ⚠ COPLANARITY APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINALS.
- DRAWING CONFORMS TO JEDEC MO220, EXCEPT EXPOSED PAD DIMENSION FOR
- T2855-3, T2855-6, T4055-1 AND T4055-2.
- △OL WARPAGE SHALL NOT EXCEED 0.10 mm.
- 11. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY.
- NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.
- ⚠ LEAD CENTERLINES TO BE AT TRUE POSITION AS DEFINED BY BASIC DIMENSION 'e', ±0.05.
- 14. ALL DIMENSIONS APPLY TO BOTH LEADED AND PHFREE PARTS.

-DRAWING NOT TO SCALE-

EXPOSED PAD VARIATIONS								
PKG.	D2			E2				
CODES	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
T1655-2	3.00	3.10	3.20	3.00	3.10	3.20		
T1655-3	3.00	3.10	3.20	3.00	3.10	3.20		
T1655N-1	3.00	3.10	3.20	3.00	3.10	3.20		
T2055-3	3.00	3.10	3.20	3.00	3.10	3.20		
T2055-4	3.00	3.10	3.20	3.00	3.10	3.20		
T2055-5	3.15	3.25	3.35	3.15	3.25	3.35		
T2055MN-5	3.15	3.25	3.35	3.15	3.25	3.35		
T2855-3	3.15	3.25	3.35	3.15	3.25	3.35		
T2955-4	2.60	2.70	2.80	2.60	2.70	2.80		
T2855-5	2.60	2.70	2.80	2.60	2.70	2.80		
T2955-6	3.15	3.25	3.35	3.15	3.25	3.35		
T2855-7	2.60	2.70	2.80	2.60	2.70	2.80		
T2955-8	3.15	3.25	3.35	3.15	3,25	3.35		
T2855N-1	3.15	3.25	3.35	3.15	3.25	3.35		
T3255-3	3.00	3.10	3.20	3.00	3.10	3.20		
T3255-4	3.00	3.10	3.20	3.00	3.10	3.20		
T3255M-4	3.00	3.10	3.20	3.00	3.10	3.20		
T3255-5	3.00	3.10	3,20	3.00	3.10	3.20		
T3255N-1	3.00	3.10	3.20	3.00	3.10	3,20		
T4055-1	3.40	3.50	3.60	3.40	3.50	3.60		
T4055-2	3,40	3,50	3.60	3,40	3.50	3,60		
T4055MN-1	3.40	3.50	3.60	3.40	3.50	3.60		

PACKAGE DUTLINE,

16,20,28,32,40L THIN QFN, 5x5x0.80mm

DOCUMENT CONTROL NO. 21-0140

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	9/07	Initial release	_
1	1/08	Removed future product asterisks, updated <i>Electrical Characteristics</i> table and <i>Typical Operating Characteristics</i> section.	1, 2, 6, 8

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